

BC212B

Amplifier Transistors

PNP Silicon

Features

- Pb-Free Packages are Available*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	-50	Vdc
Collector-Base Voltage	V_{CBO}	-60	Vdc
Emitter-Base Voltage	V_{EBO}	-5.0	Vdc
Collector Current – Continuous	I_C	-100	mA dc
Total Device Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	350 2.8	mW mW/ $^\circ\text{C}$
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	1.0 8.0	W mW/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

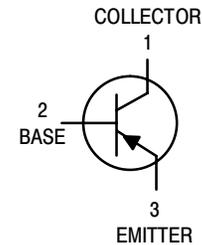
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	357	$^\circ\text{C/W}$
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	125	$^\circ\text{C/W}$

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.



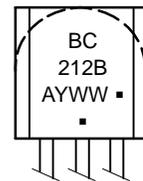
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TO-92
CASE 29
STYLE 17

MARKING DIAGRAM



BC212B = Device Code
A = Assembly
Y = Year
WW = Work Week
▪ = Pb-Free Package
(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping†
BC212B	TO-92	5000 Units / Box
BC212BG	TO-92 (Pb-Free)	5000 Units / Box
BC212BRL1	TO-92	2000 / Tape & Reel
BC212BRL1G	TO-92 (Pb-Free)	2000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

BC212B

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
Collector–Emitter Breakdown Voltage	V _{(BR)CEO}	-50	-	-	Vdc
Collector–Base Breakdown Voltage	V _{(BR)CBO}	-60	-	-	Vdc
Emitter–Base Breakdown Voltage	V _{(BR)EBO}	-5	-	-	Vdc
Collector–Emitter Leakage Current	I _{CBO}	-	-	-15	nAdc
Emitter–Base Leakage Current	I _{EBO}	-	-	-15	nAdc

ON CHARACTERISTICS

DC Current Gain (I _C = -10 μAdc, V _{CE} = -5.0 Vdc) (I _C = -2.0 mAdc, V _{CE} = -5.0 Vdc) (I _C = -100 mAdc, V _{CE} = -5.0 Vdc) (Note 1)	h _{FE}	40 60 -	- - 120	- - -	-
Collector–Emitter Saturation Voltage (I _C = -10 mAdc, I _B = -0.5 mAdc) (I _C = -100 mAdc, I _B = -5.0 mAdc) (Note 1)	V _{CE(sat)}	- -	-0.10 -0.25	- -0.6	Vdc
Base–Emitter Saturation Voltage (I _C = -100 mAdc, I _B = -5.0 mAdc)	V _{BE(sat)}	-	-1.0	-1.4	Vdc
Base–Emitter On Voltage (I _C = -2.0 mAdc, V _{CE} = -5.0 Vdc)	V _{BE(on)}	-0.6	-0.62	-0.72	Vdc

DYNAMIC CHARACTERISTICS

Current–Gain – Bandwidth Product (I _C = -10 mAdc, V _{CE} = -5.0 Vdc, f = 100 mHz)	f _T	-	280	-	MHz
Common–Base Output Capacitance (V _{CB} = -10 Vdc, I _C = 0, f = 1.0 mHz)	C _{ob}	-	-	6.0	pF
Noise Figure (I _C = -0.2 mAdc, V _{CE} = -5.0 Vdc, R _S = 2.0 kΩ, f = 1.0 kHz, f = 200 Hz)	NF	-	-	10	dB
Small–Signal Current Gain (I _C = -2.0 mAdc, V _{CE} = -5.0 Vdc, f = 1.0 kHz)	h _{fe}	200	-	400	-

1. Pulse Test: T_p 300 s, Duty Cycle 2.0%.

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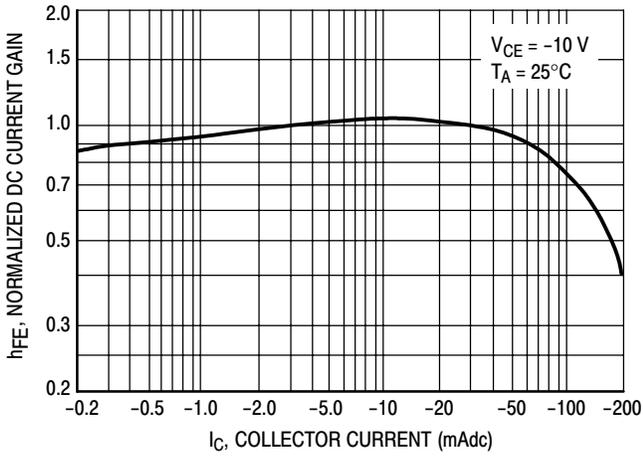


Figure 1. Normalized DC Current Gain

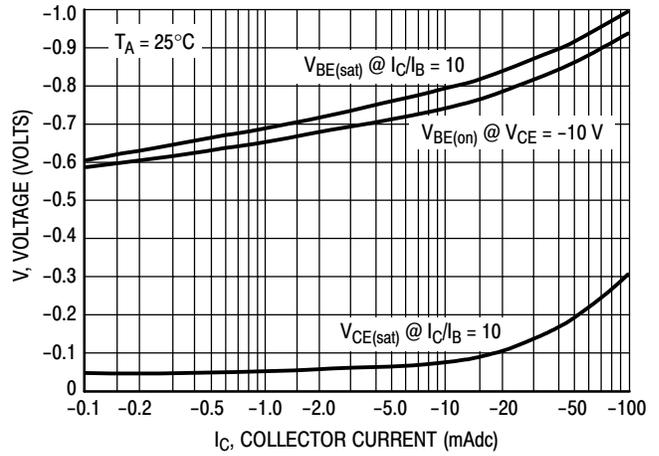


Figure 2. "Saturation" and "On" Voltages

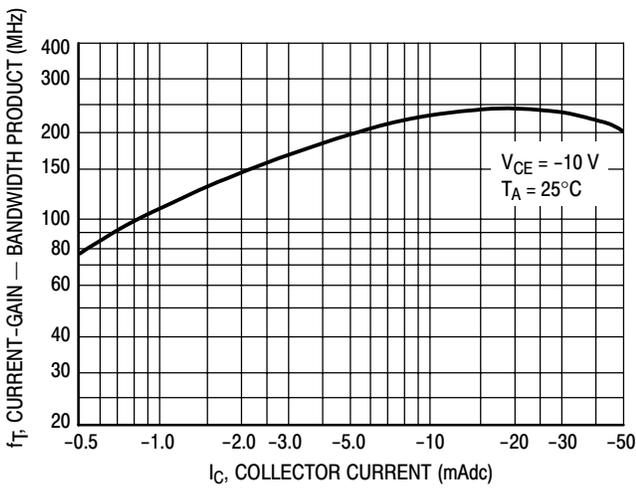


Figure 3. Current-Gain - Bandwidth Product

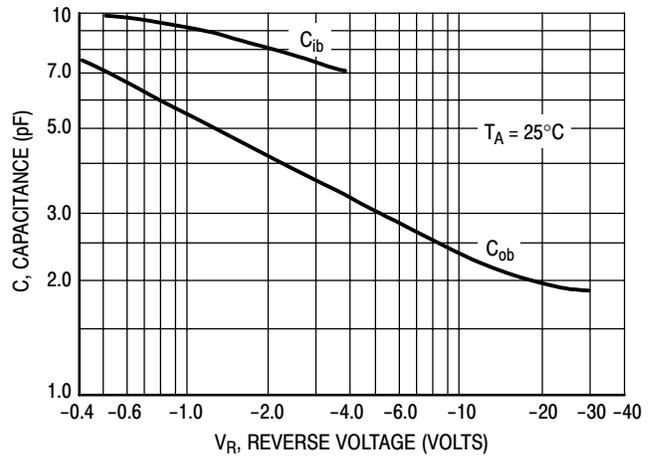


Figure 4. Capacitances

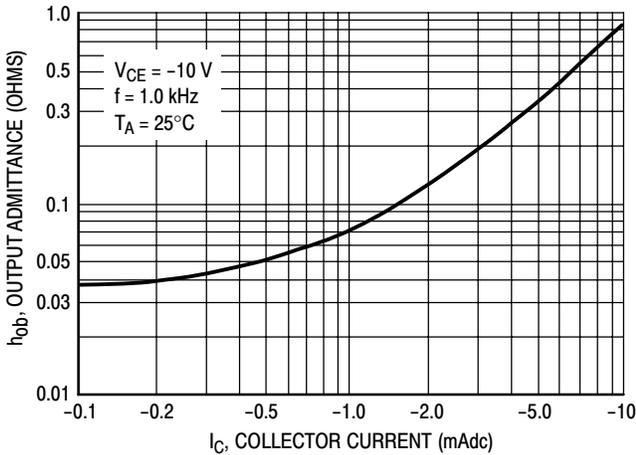


Figure 5. Output Admittance

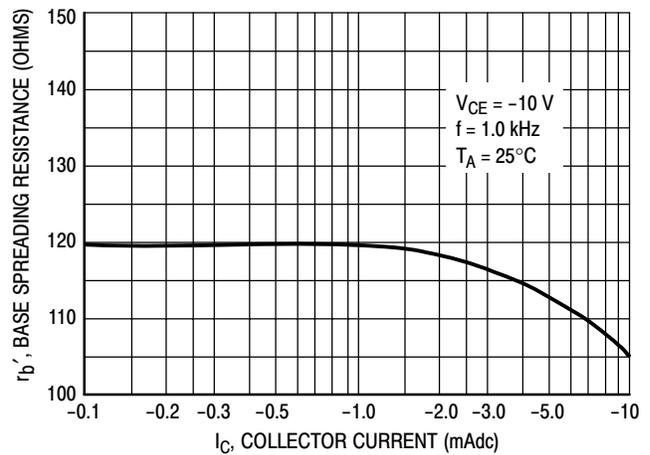
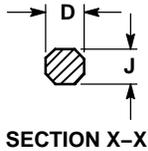
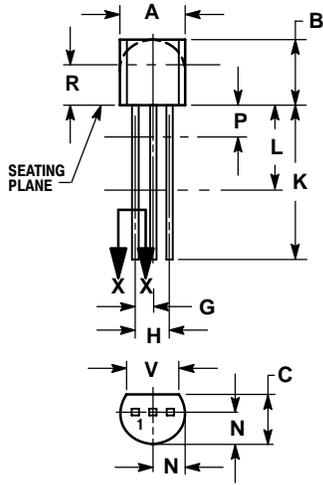


Figure 6. Base Spreading Resistance

BC212B

PACKAGE DIMENSIONS

TO-92 (TO-226)
CASE 29-11
ISSUE AL



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.175	0.205	4.45	5.20
B	0.170	0.210	4.32	5.33
C	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
H	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500	---	12.70	---
L	0.250	---	6.35	---
N	0.080	0.105	2.04	2.66
P	---	0.100	---	2.54
R	0.115	---	2.93	---
V	0.135	---	3.43	---

STYLE 17:

1. COLLECTOR
2. BASE
3. EMITTER

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